

What is claimed is:

- 5        1. A MOS array having at least one polygate supporting a plurality of sources and drains connected in parallel, wherein the polygate has a non-uniform length along its width.
2. A MOS array of claim 1, wherein the array includes a common drain interconnect and a common source interconnect.
- 10      3. A MOS array of claim 2, wherein the drain and source interconnects have a comb-like configuration.
4. A MOS array of claim 3, wherein, the drain and source interconnects are opposed and staggered to define alternating drain and source regions on either side of the polygate and extending substantially along the width of the polygate.
- 15      5. A MOS array of claim 2, wherein the drain interconnect and source interconnect each have at least one metal contact with the length of the polygate being shorter at greater distances from the at least one contact.
- 20      6. A MOS array of claim 5, wherein the array has only one drain contact and one source contact if the drain and source regions do not alternate.
7. A MOS array of claim 5, wherein the array has a drain contact on each side of the polygate and a source contact on each side of the polygate to support staggered drain and source regions.
- 25      8. A MOS array of claim 5, wherein each drain contact is located in the middle of a drain interconnect and each source contact is located in the middle of a source interconnect.
9. A MOS array of claim 8, wherein the polygate is longer in the middle and gets shorter towards the ends.

10. A MOS array of claim 1, wherein the change in length of the polygate is non-linear.
11. A MOS array of claim 9, wherein the change in length of the polygate is non-linear.
- 5 12. A MOS array of claim 10, wherein the decrease in length of the polygate further away from the drain and source contacts corresponds to the increase in resistance along the interconnect as one moves further from the drain and source contacts.
- 10 13. A MOS array of claim 11, wherein the decrease in length of the polygate further away from the drain and source contacts corresponds to the increase in resistance along the interconnect as one moves further from the drain and source contacts.

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